

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	37	((WOLFGANG) near2 (CLEMENS)).INV.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:43
S2	2	((DIETMAR) near2 (ZIPPERER)).INV.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:43
S3	551	361/523.ccls.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:44
S4	27204	capacitor and insulator and semiconductor and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:41
S6	1667	capacitor.ab. and insulator and semiconductor and electrode and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:41
S7	132	capacitor.ab. and insulator and semiconductor and electrode and organic and structured	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:42
S8	2	("3512052").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/08 14:51
S9	9	("3512052").URPN.	USPAT	ADJ	ON	2008/05/08 14:51
S10	89	("20020022284" "20020025391" "20020053320" "20020056839" "20020068392" "20020130042" "20020167003" "20020170897" "20020195644" "20030059987" "20030112576" "20030175427" "20040002176" "20040013982" "20040026689" "20040084670" "20040211329" "3512052" "3769096" "3955098" "4302648" "4340657" "4442019" "4865197" "4937119"	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/05/08 14:54

		"5173835" "5206525" "5259926" "5321240" "5347144" "5364735" "5395504" "5480839" "5486851" "5502396" "5546889" "5569879" "5574291" "5578513" "5580794" "5625199" "5630986" "5652645" "5691089" "5705826" "5729428" "5854139" "5869972" "5883397" "5892244" "5967048" "5970318" "5973598" "5994773" "5997817" "5998805" "6036919" "6045977" "6072716" "6083104" "6087196" "6133835" "6150668" "6197663" "6207472" "6215130" "6221553" "6251513" "6284562" "6300141" "6321571" "6322736" "6329226" "6330464" "6335539" "6340822" "6344662" "6362509" "6384804" "6403396" "6429450" "6498114" "6517995" "6555840" "6593690" "6603139" "6621098" "6852583").PN. OR ("7064345").URPN.			
S11	57	"5347144" "5355235").PN. OR ("5705826").URPN.	US-PPGPUB; USPAT; USOCR	ADJ	ON 2008/05/08 14:58
S12	70	capacitor, ab. and insulator layer and semiconductor layer and electrode and organic	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERVENT	ADJ	ON 2008/05/08 16:06

S13	13733	FET and capacitor same source same drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:29
S14	4685	FET and electrode and semiconductor and p near type and n near type and insulator and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:29
S15	2215	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:31
S16	882	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage and capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:31
S17	122	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage and capacitor and organic with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:34
S18	1758	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and first with semiconductor with layer and second with semiconductor with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:39
S19	359	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and first with semiconductor with layer and second with semiconductor with layer and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:01
S20	998	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:03

S21	349	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and organic and source with metal and drain with metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:05
S23	2862	capacitor and electrode and organic same semiconductor and first with semiconductor and second with semiconductor and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:25
S24	1712	capacitor and electrode and organic with semiconductor and first with semiconductor and second with semiconductor and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:25
S25	9	("3512052").URPN.	USPAT	ADJ	ON	2008/05/14 14:26
S26	1154	capacitor and electrode and organic with semiconductor and first with semiconductor with layer and second with semiconductor with layer and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:29
S27	314	(capacitor.ab. or capacitor.clm. or capacitor.ti.) and electrode and organic with semiconductor and first with semiconductor with layer and second with semiconductor with layer and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:39
S29	29476	(field effect transistor or capacitor) and (first with semiconductor) same (second with semiconductor) and electrode and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:50

S30	5067	(field effect transistor or capacitor) and (first with semiconductor) same (second with semiconductor) with electrode with (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:51
S31	3971	(capacitor) and (first with semiconductor) same (second with semiconductor) with electrode with (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:52
S32	311	361/277.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:07
S33	470	361/278.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:07
S34	223	361/281.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:35
S36	1	("5694355").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/14 16:01
S37	1	("6791402").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/14 16:02
S38	6666	FET and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 06:35
S39	7848	capacitor.ab. and insulator and semiconductor and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 06:39
S40	6666	FET and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 08:01
S41	1639	FET.ab. and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 08:03
S42	4791	FET and capacitor same source near5 connect\$4 near5 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 09:04

S43	0	FET and capacitor same source is connected to the drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 09:10
S45	460	capacitor and (insulator or dielectric) and (electrode or conductive plate) and (ptype or p near type) and (n-type or n near type) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:19
S46	5	("5384649" "5583676").PN. OR ("6219170").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/05/15 11:27
S47	27	capacitor and (insulator or dielectric) and (electrode or conductive plate) and (ptype or p near type) and (n-type or n near type) and semiconductor not silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:32
S48	0	semiconductor near3 insulator near3 semiconductor near3 (electrode or conductor or conductive plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:33
S49	1	semiconductor with insulator with (electrode or conductor or conductive plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:36
S51	44	semiconductor-insulator-semiconductor and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:42
S52	1	("5298762").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/15 11:51
S53	8	semiconductor insulator semiconductor and capacitor and ohmic contact	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:52

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